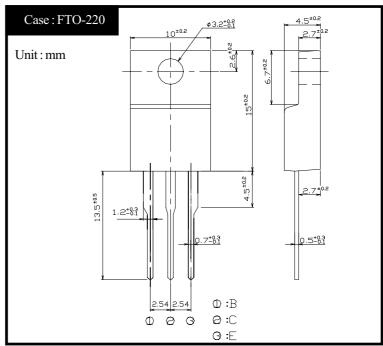
Switching Power Transistor

2SC5241

5A NPN

OUTLINE DIMENSIONS



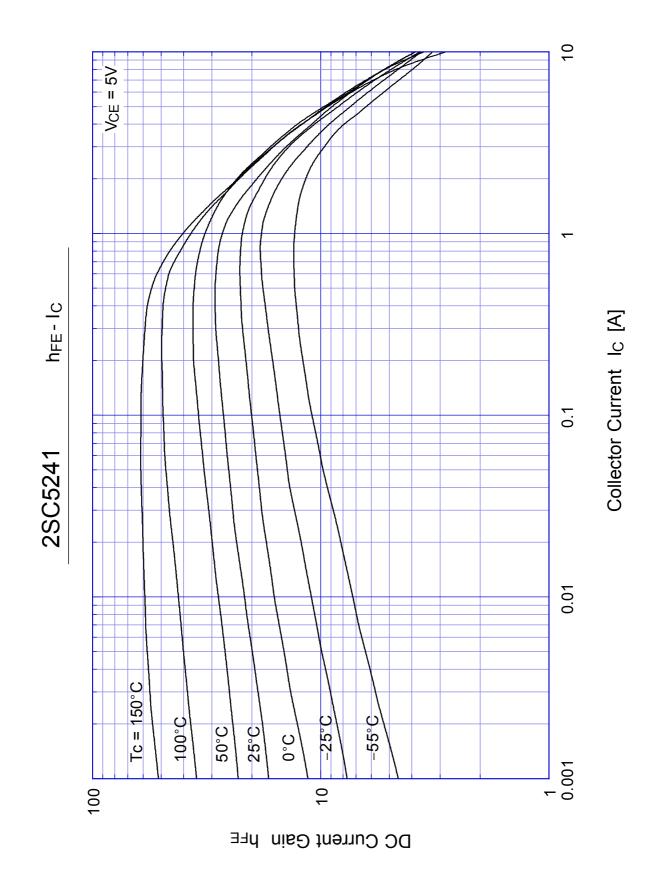
RATINGS

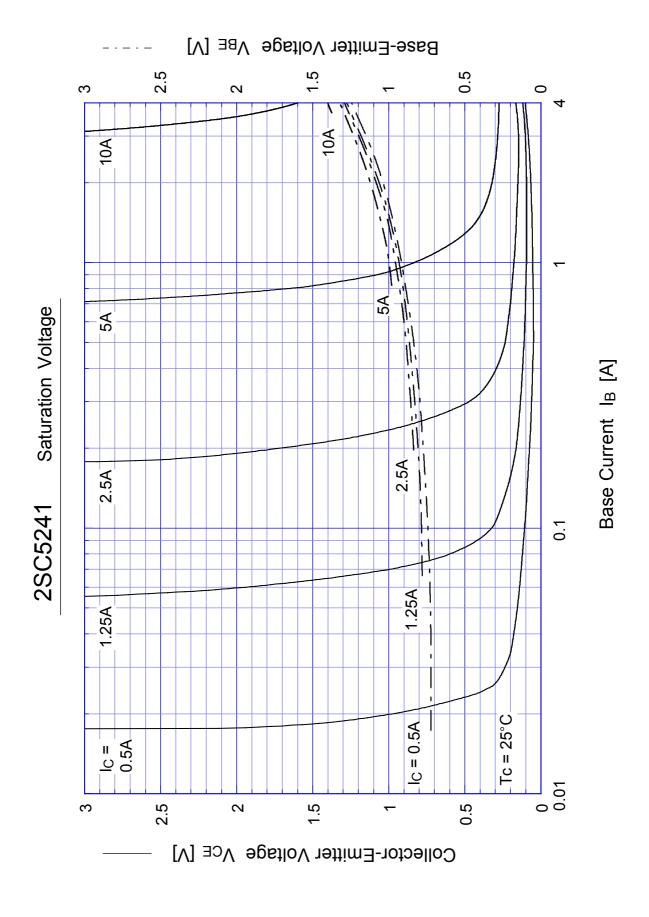
Absolute Maximum Ratings

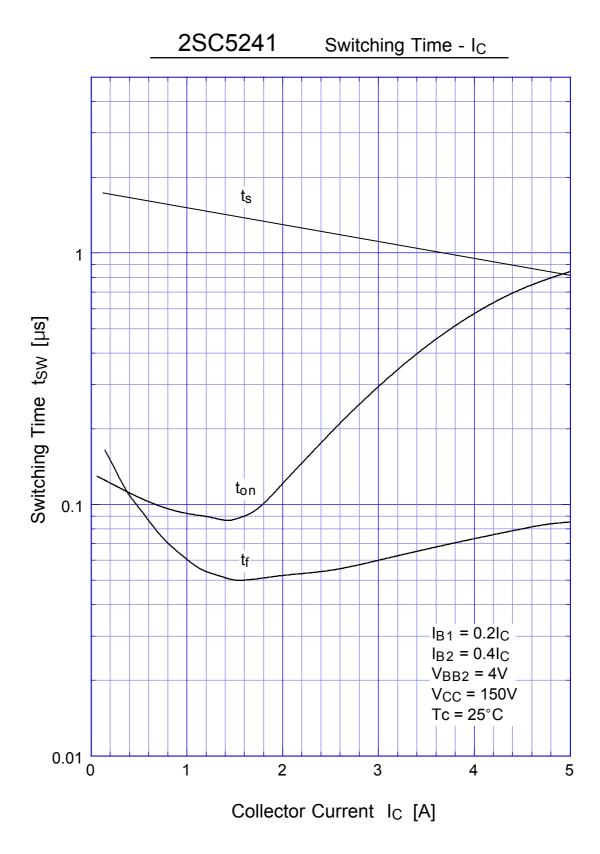
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T stg		-55~150	$^{\circ}\!\mathbb{C}$
Junction Temperature	Tj		150	$^{\circ}\!\mathbb{C}$
Collector to Base Voltage	V_{cbo}		600	V
Collector to Emitter Voltage	V_{ceo}		450	V
	V_{cex}	$V_{\rm EB} = 5V$	600	
Emitter to Base Voltage	V_{EBO}		7	V
Collector Current DC	I_{C}		5	Α
Collector Current Peak	I _{CP}		10	
Base Current DC	\mathbf{I}_{B}		2	Α
Base Current Peak	\mathbf{I}_{BP}		4	
Total Transistor Dissipation	P _T		30	W
Dielectric Strength	Vdis	Terminals to case, AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque)	0.5(0.3)	N•m

● Electrical Characteristics (Tc=25°C)

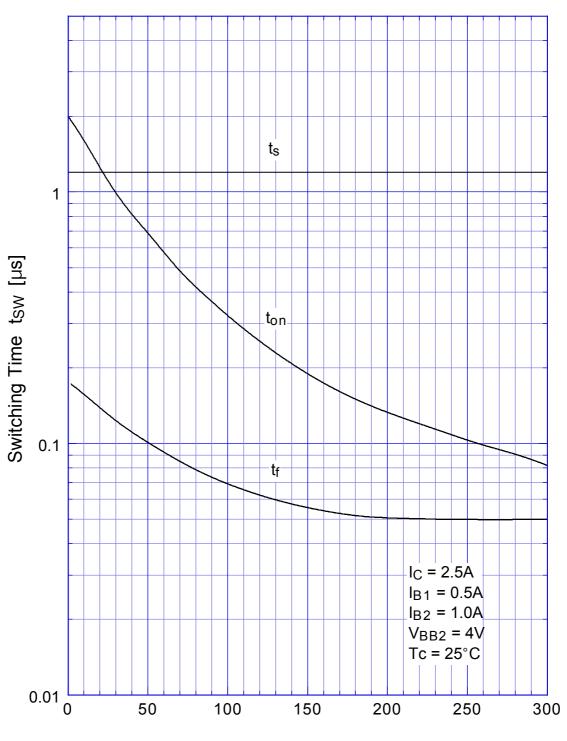
Item	Symbol	Conditions	Ratings	Unit
Collector to Emitter Sustaining Voltage	$ m V_{CEO}(sus)$	$I_{C} = 0.1A$	Min 450	V
Collector Cutoff Current	$I_{\mathtt{C}\mathrm{BO}}$	rated $V_{ exttt{CBO}}$	Max 0.1	mA
	I _{ceo}	rated V_{CEO}	Max 0.1	
Emitter Cutoff Current	$\mathbf{I}_{\mathrm{EBO}}$	rated V_{EBO}	Max 0.1	mA
DC Current Gain	$h_{ m FE}$	$V_{CE} = 5V$, $I_C = 2.5A$	M in 10	
	$h_{ m FEL}$	$V_{CE} = 5V$, $I_C = 1mA$	Min 5	
Collector to Emitter Saturation Voltage	$V_{ extsf{CE}}(extsf{sat})$	$I_{C} = 2.5A$	Max 1.0	V
Base to Emitter Saturation Voltage	$ m V_{BE}(sat)$	$I_{\mathrm{B}} = 0.5$ A	Max 1.5	V
Thermal Resistance	θ jc	Junction to case	Max 4.16	°C/W
Transition Frequency	f_{T}	$V_{CE} = 10V$, $I_C = 0.5A$	S TD 20	MHz
Turn on Time	ton	$I_{C} = 2.5A$	Max 0.5	
Storage Time	ts	$I_{B1} = 0.5A, I_{B2} = 1A$	Max 2.0	μ s
Fall Time	tf	$R_L = 60 \Omega$, $V_{BB2} = 4V$	Max 0.2	



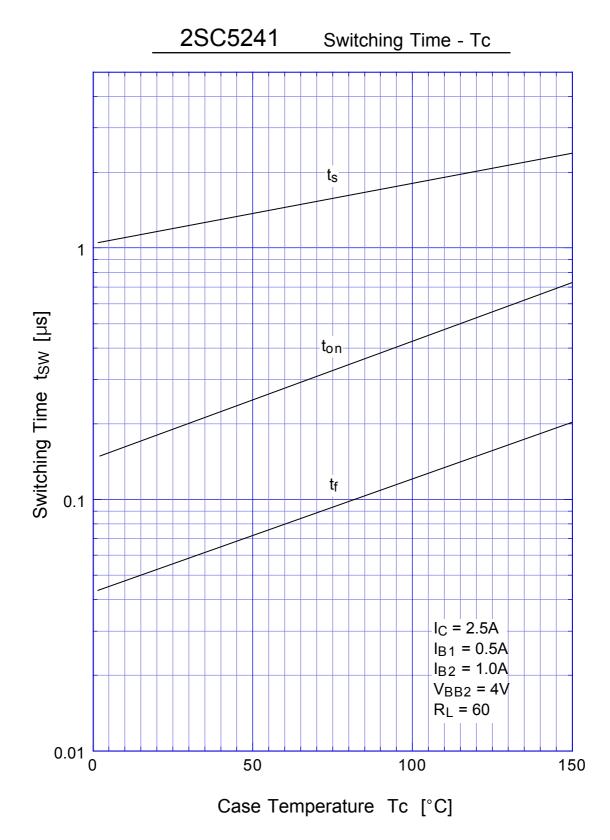


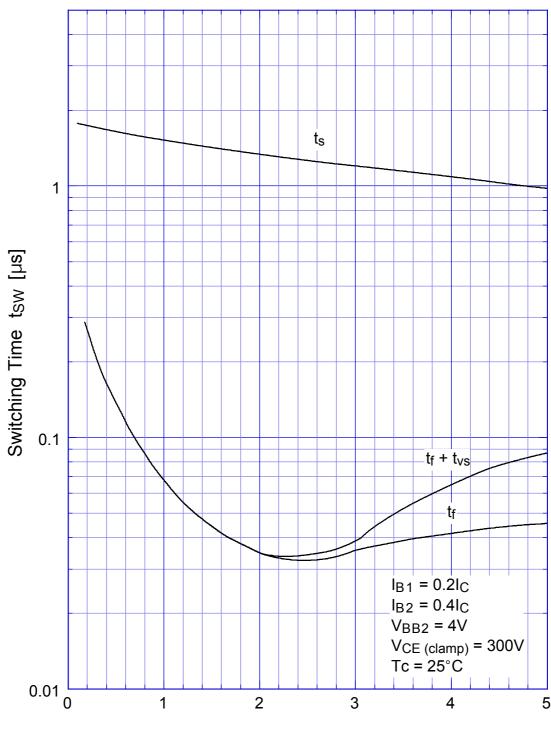






Collector Voltage V_{CC} [V]





Collector Current I_C [A]

